

MOS Field Effect Power Transistors

2SK3059

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

This product is N-Channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- · Low On-State Resistance
 - $Ros(on)1 = 15m\Omega$ Max. (VGS=10V,ID=25A)

 $R_{DS(on)2} = 23m\Omega$ Max. (VGS= 4V,ID=25A)

- Low Ciss Ciss = 2550pF Typ.
- · Built-in Gate Protection Diode
- · Isolated TO-220 Package

0.7±0.1 1.3±0.2 2.5±0.1 1.Gate 2.Drain 3.Source 1 2 3

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

			MP-45F (ISOLATED TO-220)			
Drain to Source Voltage	Voss	60	٧	,		
Gate to Source Voltage	V _{GSS}	± 20	V	Drain		
Drain Current(DC)	ID(DC)	± 50	Α	1		
Drain Current(pulse)*	D(pulse)	±200	Α	ļ.,		
Total Power Dissipation(Tc=25°C)	Рт	30	W	⊢ Body Gate		
Total Power Dissipation(T₂=25°C)	Рт	2.0	W	Gate → H Diode		
Channel Temperature	Tch	150	${\mathbb C}$			
Storage Temperature	T_{stg}	-55 to +150	${\mathbb C}$	Gate Protection		
				Diode Source		

^{*} PW≦10μs, Duty Cycle≦1%

THRMAL RESISTANCE

Channel to Case Rth(ch-c) 4.17 °C/W Channel to Ambient Rth(ch-a) 62.5 °C/W

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this deveice acutally used, an additional protection circuit is externally required if voltage exceeding the rated voltage may be applied to this device.

This information in this document is being issued in advance of the production cycle for the device. The parameter for the device may change before final production or NEC Corporation, at its own discretion, may withdraw the device prior to its production.

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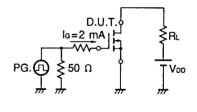
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ELECTRICAL CHARACTERISTICS(Ta=25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source	RDS(on)1	Vgs=10V, lp=25A		11	15	mΩ
On-state Resistance	RDS(on)2	Vgs= 4V, lp=25A	Į.	16	23	mΩ
Gate to Source Cutoff Voltage	Vgs(off)	Vos=10V, lo=1mA	1.0	1.5	2.0	V
Forward Transfer Admittance	yfs	Vos=10V, Io=25A	15	30		S
Drain Leakage Current	loss	Vps=60V, Vgs=0			10	μА
Gate to Source Leakage Current	lgss	Vgs=±20V, Vps=0			±10	μА
Input Capacitance	Ciss	Vos=10V		2550		рF
Output Capacitance	Coss	Vgs=0		700		pF
Reverse Transfer Capacitance	Crss	f=1MHz		250		pF
Turn-On Delay Time	td(on)	In=25A		30		ns
Rise Time	tr	Vgs(on)=10V		400		ns
Turn-Off Delay Time	td(off)	Vpp=30V		170		ns
Fall Time	tr	R _G =10Ω		200		ns
Total Gate Charge	Q _G	lo=50A		50		nC
Gate to Source Charge	Qgs	V _{DD} =48V		5.0		nC
Gate to Drain Charge	QgD	VGS(on)=10V		15		nC
Body Diode Forward Voltage	V _{F(S-D)}	I=50A,Vgs=0		1.0		٧
Reverse Recovery Time	trr	I==50A,Vgs=0		80		ns
Reverse Recovery Charge	Qrr	di/dt=100A/μs		20		nC

Test Circuit 1 Switching Time

Test Circuit 2 Gate Charge



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Anti-radioactive design is not implemented in this product.